Notice of Allowability	Application No.	Applicant(s)	
	10/072,160	SCHLUPP ET AL.	
	Examiner	Art Unit	
	Lan Vinh	1765	
The MAILING DATE of this communication appearance All claims being allowable, PROSECUTION ON THE MERITS IS herewith (or previously mailed), a Notice of Allowance (PTOL-85) NOTICE OF ALLOWABILITY IS NOT A GRANT OF PATENT RI of the Office or upon petition by the applicant. See 37 CFR 1.313	(OR REMAINS) CLOSED in this or other appropriate communics IGHTS. This application is subject and MPEP 1308.	s application. If not include ation will be mailed in due	ed course. THIS
1. A This communication is responsive to Amendment and rem.	<u>arks filed on 3/22/2004</u> .		
2. ⊠ The allowed claim(s) is/are <u>1-42</u> .	•		
3. $igotimes$ The drawings filed on <u>05 February 2002</u> are accepted by the	he Examiner.		
4. Acknowledgment is made of a claim for foreign priority una) All b) Some* c) None of the: 1. Certified copies of the priority documents have 2. Certified copies of the priority documents have 3. Copies of the certified copies of the priority documents have International Bureau (PCT Rule 17.2(a)). * Certified copies not received: Applicant has THREE MONTHS FROM THE "MAILING DATE" noted below. Failure to timely comply will result in ABANDONM THIS THREE-MONTH PERIOD IS NOT EXTENDABLE. 5. A SUBSTITUTE OATH OR DECLARATION must be subm INFORMAL PATENT APPLICATION (PTO-152) which give 6. CORRECTED DRAWINGS (as "replacement sheets") must (a) including changes required by the Notice of Draftspers 1) hereto or 2) to Paper No./Mail Date (b) including changes required by the attached Examiner's Paper No./Mail Date Identifying indicia such as the application number (see 37 CFR 1 each sheet. Replacement sheet(s) should be labeled as such in the content of the deposit of th	e been received. e been received in Application N cuments have been received in of this communication to file a reached. So the submitted when the state of the submitted of the	this national stage applicate this national stage applicate eply complying with the requirement of National State of the Office action of the 121(d). AL must be submitted. National State of the Submitted. National State of the Submitted.	quirements OTICE OF
Attachment(s) 1. ☐ Notice of References Cited (PTO-892)	5. ☐ Notice of Inform	nal Patent Application (PTC	D-152)·
2. ☐ Notice of Draftperson's Patent Drawing Review (PTO-948)	6. ☐ Interview Summ	nary (PTO-413).	, 102)
3. Information Disclosure Statements (PTO-1449 or PTO/SB/0 Paper No./Mail Date	<u></u>	endment/Comment	wanaa
 Examiner's Comment Regarding Requirement for Deposit of Biological Material 	8. ☐ Examiner's Stat 9. ☐ Other	tement of Reasons for Allo	wance
	5. <u></u> 55.	Lan Vinh AU 1765	

U.S. Patent and Trademark Office PTOL-37 (Rev. 1-04) Application/Control Number: 10/072,160

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EXAMINER'S AMENDMENT

1. An examiner's amendment to the record appears below. Should the changes and/or additions be unacceptable to applicant, an amendment may be filed as provided by 37 CFR 1.312. To ensure consideration of such an amendment, it MUST be submitted no later than the payment of the issue fee.

The application has been amended as follows:

In line 1 of claim 30, (previously amended) has been replaced with (previously presented)

Allowable Subject Matter

Claims 1-42 allowed.

The following is an examiner's statement of reasons for allowance:

The reason for allowance of claim 1 has been stated in the previous final office action (paper no. 1203). Regarding claims 10, 29, the applicants have presented a persuasive argument, see the second and third paragraph on page 12 of the response filed 3/22/2004 that the combination of the closest cited prior art of Lin et al (US 6,057,207) and Parat et al (US 6,194,784) does not disclose or suggest a method for processing a semiconductor substrate comprises the step of depositing a trench oxide that both fills one or more trenches separating first and second device regions of a substrate and covers a first nitride layer disposed above a first oxide layer because adding the step of forming a reflowed dielectric layer as per Parat over Lin's nitride etch

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barrier layer 44/first nitride layer would have covered Lin's high areas 40 thereby destroying Lin's process.

Any comments considered necessary by applicant must be submitted no later than the payment of the issue fee and, to avoid processing delays, should preferably accompany the issue fee. Such submissions should be clearly labeled "Comments on Statement of Reasons for Allowance."

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Conclusion

2. Any inquiry concerning this communication or earlier communications from the examiner should be directed to Lan Vinh whose telephone number is 571 272 1471. The examiner can normally be reached on M-F 8:30-5:30 PM.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Nadine Norton can be reached on 571 272 1465. The fax phone number for the organization where this application or proceeding is assigned is 703-872-9306.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

LV

April 1, 2004